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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Toshihisa YOKOYAMA, Ken-ichi NODA, Katsuhiko IMAI
and Minoru IMAEDA

Ser. No.: 09/854,924

Group Art Unit: 1765

Filed: May 14, 2001

Examiner: Song, M.

Confirmation No.: 7936

For: PROCESS AND APPARATUS FOR PRODUCING AN OXIDE SINGLE
CRYSTAL

RULE 132 DECLARATION OF KATSUHIRO IMAI

#14
4/16/03
mw

I, Katsuhiko IMAI, hereby declare and state that:

1. I received a Doctor of Science degree in Mineralogy in March, 1993 from the University of Tokyo.
2. I have been employed by NGK Insulators, Ltd., the assignee of the above identified application, since April, 1993. During my employment with NGK, I have been involved with research and development of: single crystal materials at the Research Laboratory of NGK Insulators, Ltd., from April, 1993.
3. I have reviewed the prosecution history of the above-identified application, particularly the Final Office Action mailed January 15, 2003 and the Advisory Action mailed March 28, 2003. I have also reviewed Imaeda et al. and Ciszek et al., the applied prior art of record.

4. In the Advisory Action, the Examiner is taking the position that Applicants have not provided evidentiary support for the arguments that: 1) silicon crystals typically have a higher coefficient of thermal conductivity compared to that of oxide single crystals; and 2) silicon crystals typically have a lower coefficient of thermal expansion compared to that of oxide single crystals.

5. With reference to The Chemical Society of Japan (1993): *Kagaku Binran Kiso-hen II* (Handbook of Chemistry, Fundamental Chemistry Volume II), 4th edition, Maruzen, Tokyo (in Japanese), a data sheet obtained from the INRAD, Inc., website http://www.inrad.com/pdf/Inrad_datasheet_LNB.pdf (a printout of which is attached hereto), oxide single crystals typically have a coefficient of thermal conductivity of 4W/m·K and coefficients of thermal expansion of $14.1 \times 10^{-6}/K(//a)$ and $4.1 \times 10^{-6}/K(//c)$, whereas silicon crystals typically have a coefficient of thermal conductivity of 148W/mK and a coefficient of thermal expansion of $4.15 \times 10^{-6}/K$. Therefore, those of ordinary skill in the art understand that silicon crystals have a higher coefficient of thermal conductivity and a lower coefficient of thermal expansion in comparison to oxide single crystals.

6. The Imaeda et al. reference relates to oxide single crystals and that reference correctly recognizes that it is undesirable to have too high of a cooling rate after growing the oxide single crystals. Although Imaeda et al. do not specifically address cooling oxide single crystals at the liquid-solid crystal interface, based on the disclosure in Imaeda et al., I would also conclude that one should not use a cooling gas to directly cool the oxide single crystal liquid-solid crystal interface. This is because the temperature at the liquid-solid crystal interface is necessarily higher than the temperature of the grown crystal body, and thus, blowing a cooling gas directly on the oxide single crystal solid-liquid crystal interface

would necessarily produce a greater rate of temperature change at the hotter liquid-solid crystal interface than would be realized if the same cooling medium were blown on the cooler crystal body. Therefore, for the same reasons that it is undesirable to have too high of a temperature gradient in the grown crystal body after crystal growth, as specifically disclosed by Imaeda et al., it is also undesirable to have too high of a temperature gradient at the liquid-solid crystal interface.

7. Ciszek deals with a method of producing a silicon crystal, which includes a step of directing a cooling medium onto the liquid-solid crystal interface portion. Ciszek's method is successful because of the relatively higher coefficient of thermal conductivity and the relatively lower coefficient of thermal expansion compared to those of oxide single crystals (see paragraph 5 above). On the other hand, blowing a cooling medium onto the liquid-solid crystal interface of Imaeda's oxide single crystal would not necessarily produce the benefits disclosed in Ciszek, because of the relatively lower coefficient of thermal conductivity and the relatively higher coefficient of thermal expansion of oxide single crystals. Therefore, skilled artisans would not conclude that oxide single crystals could withstand Ciszek's liquid-solid crystal interface cooling treatment, which, again, is designed for silicon crystals, because oxide single crystals have a lower coefficient of thermal conductivity and a higher coefficient of thermal expansion in comparison to silicon crystals.

8. Based on my academic credentials and work experience, I consider myself to be one of ordinary skill in the art. The claimed invention was not obvious to me at the time it was made. Nor do I believe that the claimed invention would have been obvious to others of ordinary skill in the art absent our discovery.

9. I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

April 9, 2003
Date

Katsuhiro Imai
Katsuhiro Imai

INRAD Lithium Niobate

Lithium Niobate (LiNbO₃)

PHYSICAL PROPERTIES

Chemical Formula

LiNbO₃
congruently melting¹

Crystal Symmetry and Class

trigonal, R3c

Point Group

3m

Lattice Constants²

a = 5.15052(6) Å

c = 13.86496(3) Å

Density²

4.640(5) g/cm³

Moh's Hardness

5

Fracture Toughness³

x-face

1.07 MPam^{1/2}

y-face

1.17 MPam^{1/2}

0.67 MPam^{1/2}

Elastic Compliance⁴ at Constant Polarization (S_p) and at Constant Field (S_E) and Temperature Dependence⁵

(TPa) ⁻¹	(TPa) ⁻¹	(10 ⁻⁴ /°K)
S _{P11} = 4.76	S _{E11} = 5.78	(1/S _{E11})dS _{E11} /dT = 1.66
S _{P12} = -0.80	S _{E12} = -1.01	(1/S _{E12})dS _{E12} /dT = 0.78
S _{P13} = -1.20	S _{E13} = -1.47	(1/S _{E13})dS _{E13} /dT = 1.94
S _{P14} = 1.02	S _{E14} = -1.02	(1/S _{E14})dS _{E14} /dT = 1.33
S _{P33} = 4.10	S _{E33} = 5.02	(1/S _{E22})dS _{E22} /dT = 1.60
S _{P44} = 9.3	S _{E44} = 17.0	(1/S _{E44})dS _{E44} /dT = 2.05
S _{POO} = 10.5	S _{EOO} = 13.6	(1/S _{EOO})dS _{EOO} /dT = 1.43

Stiffness⁴ at Constant Polarization (C_p) and at Constant Field (C_E) and Temperature Dependence⁵

(GPa)	(GPa)	(10 ⁻⁴ /°K)
C _{P11} = 219	C _{E11} = 203	(1/C _{E11})dC _{E11} /dT = -1.74
C _{P12} = 37	C _{E12} = 53	(1/C _{E12})dC _{E12} /dT = -2.52
C _{P13} = 76	C _{E13} = 75	(1/C _{E13})dC _{E13} /dT = -1.59
C _{P14} = -15	C _{E14} = 9	(1/C _{E14})dC _{E14} /dT = -2.14
C _{P22} = 252	C _{E22} = 245	(1/C _{E22})dC _{E22} /dT = -1.53
C _{P44} = 95	C _{E44} = 60	(1/C _{E44})dC _{E44} /dT = -2.04
C _{POO} = 91	C _{EOO} = 75	(1/C _{EOO})dC _{EOO} /dT = -1.43

INRAD Lithium Niobate

OPTICAL AND ELECTRO-OPTICAL PROPERTIES

Optical Symmetry uniaxial negative

Optical Transmission 0.400 μm - 5.0 μm

Sellmeier Equation Constants¹³

$$n = (A + B/(\lambda^2 + C) + D\lambda^2)^{1/2}; \quad \lambda \text{ in microns}$$

$$\begin{array}{llll} n_o & A=4.9048 & B=0.11768 & C=-0.0475 & D=-0.027169 \\ n_e & A=4.582 & B=0.099169 & C=-0.044432 & D=-0.02195 \end{array}$$

Calculated Refractive Index Values¹³

$$\begin{array}{ll} n_o(1.064 \mu\text{m}) = 2.2322; & n_e(1.064 \mu\text{m}) = 2.1560 \\ n_o(2.060 \mu\text{m}) = 2.1949; & n_e(2.060 \mu\text{m}) = 2.1243 \\ n_o(3.500 \mu\text{m}) = 2.1405; & n_e(3.500 \mu\text{m}) = 2.0788 \end{array}$$

Photoelastic Strain Coefficients at Constant Field¹¹

$$\begin{array}{ll} p_{11} = -0.026 & p_{31} = 0.17 \\ p_{12} = 0.08 & p_{32} = 0.07 \\ p_{13} = 0.13 & p_{41} = -0.151 \\ p_{14} = -0.08 & p_{44} = 0.146 \end{array}$$

Temperature Variation of Refractive Index¹³ for $\lambda = 1.0 \mu\text{m} - 4.0 \mu\text{m}$

$$\begin{array}{l} dn_o/dT = 3.3 \times 10^{-5}/^\circ\text{C} \\ dn_e/dT = 37 \times 10^{-5}/^\circ\text{C} \end{array}$$

Nonlinear d Coefficients^{12,20}

$$\begin{array}{l} d_{22} = 2.4 \text{ pm/V} \\ d_{31} = -4.52 \text{ pm/V} \\ d_{33} = 31.5 \text{ pm/V} \end{array}$$

Effective Nonlinear Optical Coefficient

$$d_{\text{eff}} = d_{31} \sin\theta - d_{22} \cos\theta \sin 3\phi$$

Electro Optic Coefficients @ 0.633 μm ²³

$$\begin{array}{ll} r_{13}^I = 10 \text{ pm/V} & r_{13}^S = 8.6 \text{ pm/V} \\ r_{22}^T = 6.8 \text{ pm/V} & r_{22}^S = 3.4 \text{ pm/V} \\ r_{32}^T = 32.2 \text{ pm/V} & r_{32}^S = 30.8 \text{ pm/V} \\ r_{51}^T = 32 \text{ pm/V} & r_{51}^S = 28 \text{ pm/V} \end{array}$$

Variation of Electro Optic Coefficient r_{22} with Wavelength²²
And Calculated Half-wave Voltage For 9mmx9mmx25mm Q-Switch

$$V_{1/2} = \lambda d / (4 n^3 r_{22})$$

r_{22}^T	$V_{1/2}$
1.064 μm = 5.6 pm/V	1.55 kVolts
1.318 μm = 5.4 pm/V	2.02 kVolts
1.55 μm = 5.3 pm/V	2.44 kVolts
2.10 μm = 5.2 pm/V	3.45 kVolts
2.79 μm = 5.1 pm/V	4.78 kVolts
2.94 μm = 5.1 pm/V	5.08 kVolts

Damage Threshold²

$$3 \text{ J/cm}^2 \text{ @ } 10 \text{ nsec}$$

INRAD Lithium Niobate

THERMAL AND ELECTRICAL PROPERTIES

Melting Point ⁷	1240° C
Curie Temperature ⁸	1145° C
Thermal Conductivity ⁹	4. W/m°K
Thermal diffusivity ⁶	$9 \times 10^{-7} \text{ m}^2/\text{sec}$
Specific Heat ⁹	0.633 J/g°K
Thermal Expansion ¹⁰	$\alpha_a = 14.1 \times 10^{-6} / ^\circ\text{K}$ $\alpha_c = 4.1 \times 10^{-6} / ^\circ\text{K}$
Resistivity ¹⁴	$2 \times 10^{10} \Omega \cdot \text{cm}$ @ 200° C

Dielectric Constants¹⁵

$K_{11}^S = 4.4$	$K_{11}^T = 1.8$
$K_{33}^S = 28$	$K_{33}^T = 32$

Loss tangent¹⁹ @100 °C

x-axis	$\tan \delta = 0.0006$
y-axis	$\tan \delta = 0.001$

Typical Polish Specifications

Wavefront Distortion:	$\lambda / 8$ @ 633 nm
Flatness:	$\lambda / 10$ @ 633 nm
Parallelism:	1 arcseconds
Scratch - Dig:	10 - 5

INRAD Lithium Niobate

Description

Lithium niobate is a ferroelectric material suitable for a variety of applications. Its versatility is made possible by the excellent electro-optic, nonlinear, and piezoelectric properties of the intrinsic material. It is one of the most thoroughly characterized electro-optic materials, and crystal growing techniques consistently produce large crystals of high perfection.

Applications that utilize the large electro-optic coefficients of lithium niobate are optical modulation and Q-switching of infrared wavelengths. Because the crystal is nonhygroscopic and has a low half-wave voltage, it is often the material of choice for Q-switches in military applications. The crystal can be operated in a Q-switch configuration with zero residual birefringence and with an electric field that is transverse to the direction of light propagation. Because piezoelectric ringing can be severe, piezoelectrically damped designs can be very useful. The damage threshold of the intrinsic material at 1.06 microns with a 10 nsec pulse is approximately 3 J/cm². With appropriate AR coatings, a surface damage threshold of 300-500 MW/cm² can be achieved for the same conditions.

Applications that use the large nonlinear d coefficient of LiNbO₃ include optical parametric oscillation, difference frequency mixing to generate tunable infrared wavelengths, and second harmonic generation. With a broad spectral transmission, which ranges from 0.4 μ m to 5.0 μ m with an OH⁻ absorption at 2.87 μ m, a large negative birefringence, and a large nonlinear coefficient, phase matching is an effective way to generate tunable wavelengths over a broad wavelength range.

Lithium niobate is particularly effective for second harmonic generation of low power laser diodes in the 1.3 to 1.55 μ m range.

For infrared generation by difference frequency mixing, the peak power limit is considerably lower than for 1.064 μ m, being about 40 MW/cm². Efficiencies for difference frequency mixing generally are smaller than shg efficiencies with KDP or BBO, which is due to the lower peak powers that can be tolerated by the crystal and the fact that the longer wavelength photons that are generated in the process are less energetic. Typical powers for 10 nanosecond long pulses with 5 mm diameter beams are 30 mJ/pulse of 0.640 μ m minus 40 mJ/pulse of 1.064 μ m to produce 2.5 mJ/pulse at 1.54 μ m, and 32 mJ/pulse of 0.532 μ m minus 32 mJ/pulse of 0.640 μ m to produce 0.25 mJ/pulse at 3.42 μ m.

INRAD offers lithium niobate in a variety of configurations. Standard cuts are available as OPO crystals, Q-switches, difference frequency mixing crystals, autocorrelation crystals, and optical waveguide wafers.

Please consult an INRAD sales engineer for assistance in crystal selection and packaging.

At INRAD, all crystal growth, orientation, fabrication, polishing, and testing of LiNbO₃ is done at one site so that you are assured of complete traceability and satisfaction with every crystal that you purchase.

INRAD Lithium Niobate

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5-2 膨張率と圧縮率

5-2-1 固体単体の線膨張率および体膨張率

セルシウス温度が0度および θ における長さおよび体積を、それぞれ l_0 および l 、 v_0 とすれば、一般に線膨張率 β および体膨張率 α はそれぞれ

$$\beta = \frac{1}{l_0} \frac{dl}{d\theta} \quad (5-1)$$

$$\alpha = \frac{1}{v_0} \frac{dv}{d\theta} \quad (5-2)$$

$$\beta = \frac{1}{l_0} \frac{l_2 - l_1}{\theta_2 - \theta_1} \quad (5-3)$$

$$\alpha = \frac{1}{v_0} \frac{v_2 - v_1}{\theta_2 - \theta_1} \quad (5-4)$$

で与えられる。さらに精密な目的に対しては

$$l = l_0 (1 + \beta_1 \theta + \beta_2 \theta^2 + \beta_3 \theta^3) \quad (5-5)$$

$$v = v_0 (1 + \alpha_1 \theta + \alpha_2 \theta^2 + \alpha_3 \theta^3) \quad (5-6)$$

で表わされる。なお立方性の物質では $\alpha = 3\beta$ である。

表 5-25 固体単体の線膨張率 β ¹⁾

物質	θ °C	β または α $10^{-6} K^{-1}$	物質	θ °C	β または α $10^{-6} K^{-1}$	物質	θ °C	β または α $10^{-6} K^{-1}$
Ag	-150~0	0.170	Po	0~898	0.1375	Pa	0~300	0.106
Al	-190~0	0.103	Si	216~232	0.120	Pb	0~100	0.0999
As	-190~0	0.180	Ga	-72.3~18	0.53	Pb	0~600	0.0994
Br	0~100	0.237	Ge	0~400	0.077	Rb	20	0.953
C	20~300	0.258	Hg	-182~-79	0.470	Rb	12~220	0.085
Ca	0	0.43	I	0	0.375	Sn	0~50	0.095
Ca	6	0.09	I	-80~25	2.20	Sn	13~32	0.0975
Ca	-190~0	0.131	La	0~100	0.56	S	-272~-185	0.71
Co	0~100	0.142	Ir	0~100	0.0553	S	-195~-79	1.50
Co	20	0.15	K	0~50	0.83	S	-79~18	1.80
Bi	20~240	0.102	La	0~300	0.065	Se	(mp)	3.50
Bi	20~240	0.120	Li	0~96	0.56	Se	20~100	0.1717
Br	-273~-194	2.00	Mg	16~35	0.271	Se	0	0.090
ダイヤモンド	0~70	0.0123	Mg	0	0.243	Si	10~50	0.0415
黒鉛	20~40	0.05963	Mn	-20~0	0.2163	Sn	0~20	0.0909
銅	1000~1600	0.0093	Mn	0~100	0.051	Sn	0~20	0.1583
銅	1000~1600	0.0009	Na	0	0.086	Ta	20~1007	0.005
Fe	20~100	0.526	Na	0~100	0.71	Ta	0	0.067
Fe	0	0.234	Ni	-57.6~	2.78	Te	0~20	0.016
Fe	20~100	0.126	Ni	0~100	0.126	Te	0	0.272
Fe	100~200	0.136	Os	500~600	0.165	Tl	0~100	0.294
Fe	0~100	0.084	Os	600~900	0.178	Tl	100~200	0.308
Fe	~20	0.97	P	0~100	0.070	W	0~100	0.045
Fe	-185~-103	0.121	P	-79~19	2.75	Zn	20~250	0.530
Fe	-103~0	0.154	Pb	24~60	5.60	Zr	0	0.160
Fe	0~101	0.162	Pb	0~100	3.280	Zr	-20~0	0.0563
Fe	300	0.175	Pb	20~300	0.313	Zr	0~100	0.433

1) "Landolt-Börnstein Zahlenwerte und Funktionen aus Physik, Chemie, Astronomie, Geophysik und Technik", 6 Aufl., II Band, 1 Teil, S. 379~448, Springer-Verlag (1971).

* 1 体膨張率 α または β を意味す。

* 2 単位

5-2-2 化合物の線膨張率および体膨張率

表 5-26 固体化合物の体膨張率 α および線膨張率 β (1)

化合物	θ °C	α または β $10^{-6} K^{-1}$	化合物	θ °C	α または β $10^{-6} K^{-1}$	化合物	θ °C	α または β $10^{-6} K^{-1}$
固体無機化合物			H ₂ O (氷)	-79	0.576	KI	-79~0	1.25
Al ₂ O ₃	20~150	1.03		0	0.558	KMnO ₄	-78~18	2.20
Al ₂ O ₃	20~800	0.000	H ₂ SO ₄ · H ₂ O	-78~0	1.20	KNO ₃	-78~18	2.10
AsCl ₃	20~150	0.60	KBr	-79~0	1.10	KOH	30~120	1.05
AsCl ₃	20~150	0.67	KCl	-78~25	1.01	K ₂ SO ₄	-78~21	1.30
As ₂ O ₃	30~75	0.71	KClO ₃	-78~21	2.20	MgO	30~75	0.133

* 線膨張率 β または α を意味す。

"Landolt-Börnstein Zahlenwerte und Funktionen aus Physik, Chemie, Astronomie, Geophysik und Technik", 6 Aufl., II Band, 1 Teil, S. 469~773, Springer-Verlag (1971).

表 6-63 固体半導体の熱伝導率 $\kappa/W \cdot m^{-1} \cdot K^{-1}$

固 体	温 度 T/K							固 体	温 度 T/K						
	50	100	200	300	400	700	1000		50	100	200	300	400	700	1000
As	700	400	430	427	420	397	374	Mo	300	178	143	138	124	122	112
As ₂ S ₃	420	345	337	315	312	298	278	Nb	108	132	138	132	105.57	(71.5)	(52.3)
B	404	160	92.5	27.5	12.7	8.41	5.29	Nb ₂ O ₅	76	55.2	52.8	53.7	53.2	53.8	64.4
Bc	4000	300	301	200	161	115	89.7	Nd	336	158	168	164	168	10.1	21.5
B(1-4)	36.7	18.8	11.3	9.15	8.22	(24.1)	(16.2)	Ni	245	112	90.8	87.4	86.9	65.4	71.8
(2-3)	2650	1010	1430	990	632			Os	42.7	38.7	37.7	12.1			86.3
(4-5)	9300	10000	4040	2310	1530			P(As)	41.5	28.5	35.6	35.2	23.8	(17.0)	(71.5)
(6-7)	3900	3450	2260	1350	936			Pb	123	77.3	75.5	75.5	75.5	75.5	75.5
(8-9)	17	53	120	129	118	86	64	Pr	62.7	61.3	51.9	58.2	(23.1)	(28.9)	(23.7)
(10-11)	19	42	88	98	90	67	49	Sb	96.2	59.9	51.0	46.3	46.3	46.3	44.5
(12-13)	2300	4980	1250	7400	140	750	530	Se	370	186	154	150	146	131	121
(14-15)	103	39	15	9.5	7.0	3.8	2.5	Sn	490	154	118	117	115		
(16-17)	120	101	99.3	98.8	94.7	(49.0)	21.4	S	0.977	0.522	0.255	0.255	(0.132)		
(18-19)	3.79	6.00	5.00	11.4	12.3	10.0	65.3	Sb	94.2	41.4	30.2	24.3	21.2	17.4	(27.0)
(20-21)	238	164	122	99.3	84.8		11.2	Se	115	14.3	15.3	15.3			
(22-23)	317	156	111	80.3	57.3	75.7	65.3	Si	2630	884	269	219	219	50.0	31.2
(24-25)	44.7	20.7	25.8	33.3	(20.3)	(20.3)	(17.2)	Sm	7.52	7.35	11.7	12.1	13.3		
(26-27)	11.5	10.5	9.33	10.7	10.9	12.8	15.2	Ta	113	65	73.2	80.6	82.2	(34.2)	(40.5)
(28-29)	8.28	11.9	14.3	14.3	13.9	12.6	15.8	Tb	72	58.2	57.5	57.3	57.2	59	60.2
(30-31)	372	132	94	80.3	69.4	48.7	32.5	Tc(As)	14.7	11	9.98	10.1			
(32-33)	63.6	47.1	42.4	40.5	(37.0)			Ti	47.4	25.9	21.0	21.0	21.0	21.0	
(34-35)	19.0	11.5	8.98	9.28	10.1			Tl	62.3	44.8	40.6	40.1	40.1	40.1	
(36-37)	615	232	96.8	59.8	43.2	22.1	17.4	Tm	40.1	31.8	24.6	21.9	20.1	19.4	20.7
(38-39)	26.1	20.0	14.4	13.0	82.5	31.0	24.7	U	62.8	55.6	49.4	46.1	43.8		
(40-41)	35.4	32.0	28.0	(24.0)	(9.80)	(12.7)	11.7	V	10.3	13.5	15.2	16.3			
(42-43)	7.77	7.62	13.0	13.0	13.1	(0.114)	(0.058)	Y	18.9	71.7	25.1	27.6	29.6	31.6	33.9
(44-45)	104	87.8	89.7	81.7	74.5	41.4	52.4	Yb	48.5	35.7	31.5	31.5	32.1	35.2	38.6
(46-47)	472	172	153	147	146	135	126	Zn	16.5	12.7	15.5	16.2	16.9	20.3	23.5
(48-49)	112	107	104	102	(32.0)	(10.4)	(31.3)	Zr	273	124	129	121	116	(60.04)	(67.2)
(50-51)	0.42	9.78	11.8	13.5	14.9	12.4	22.3		49.7	33.2	26.2	22.7	21.6	20.8	23.7
(52-53)	235	116	88.1	75.8	72.1	(50.9)	(60.0)								
(54-55)	20.9	16.9	17.2	16.2											
(56-57)	375	169	169	156	138	147	(50)								
(58-59)	1.05	5.79	7.17	7.92											

1 表中の () を付けた数値は融解点の値である。

2 物質名に付けた 1, 2, 3 など、単結晶試料の c 軸に平行、b 軸に平行を示す。ただし、c (高圧) については、A, T, 2 軸の加熱圧力時の圧縮方向に対する記号 (1), 平行 (2) を示し、L (圧力) は斜角異質性を示す。

表 6-64 ガラスと酸化塩の熱伝導率 $\kappa/W \cdot m^{-1} \cdot K^{-1}$

固 体	温 度 T/K							固 体	温 度 T/K						
	100	200	300	400	500	700	1000		100	200	300	400	500	700	1000
ピクサス								MEU	270	94	60	43.1	32		
SiO ₂	0.69	1.14	1.38	1.51	1.62	1.92	2.67	SiO ₂							
ス								(石英 c 軸)	39	16.4	10.4	7.6	6.0	4.5	
PYREX 7740 ¹⁾	0.58	0.90	1.10	1.22	1.35	1.65		(石英 c 軸)	20.0	9.5	6.2	4.7	3.9	3.1	
ロセラム								ThO ₂			10.2	10.2	8.1	5.5	3.7
6000 ²⁾	5.42	4.74	3.99	3.05	3.45	3.19	2.97	TiO ₂							
メ								(ルチル c 軸)	23.5	13.7	10.4	8.5			
ナフタイア	450	92	80	32.4	24.2	12.4	10.5	(ルチル c 軸)	16.9	9.7	7.4	6.0			
オシロ	133	55	36	26.4	20.2	12.6	7.9	(多結晶)			8.6	7.0	5.9	4.4	3.5
		22.4	19.6	14.6	9.7	4.7		UO ₂	6.0	8.6	8.2	7.4	6.5	5.1	3.8

Coming 社製, $\rho = 2.276 \text{ g/cm}^3$ Coming 社製, $\rho = 2.601 \text{ g/cm}^3$